EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4369	257/40.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 10:49
L2	2813	257/295.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 10:49
L3	2298	257/e27.104,e51.007. ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 10:49
L4	8577	L1 or L2 or L3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 10:49
L5	1322	L4 and (gate with capacitor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 10:49
L6	7255	L4 not L5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 10:49
L9	2334	L6 and @py< "2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 10:50

L10	4921	L6 not L9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 10:50
L12	2463	10 and @py<"2007"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 10:51
L13	2458	10 not 12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/12 11:11
S1	2	"20090039341"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/07 23:06
S2	2	WO2005064681$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/07 23:40
S3	0	ep1700342$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/07 23:41
S4	2	ep adj "1700342"$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/07 23:41
S5	9063	ferroelectric with memory with capacitor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/07 23:43

S6	9926	ferroelectric with (transisor or gate) memory with (capacitor near4 dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/07 23:44
S7	13797	ferroelectric with (transistor or gate) memory with (capacitor near4 dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/07 23:45
S8	433	ferroelectric with (transistor or gate) with (capacitor near4 dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/07 23:45
S9	126	(gate adj dielectric) with (capacitor near2 dielectric) with "same"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/07 23:46
S10	4	S8 and S9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/07 23:46
S11	1	EP001700342A2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 16:58
S12	5	"2005064681"$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:08
S13	0	JP5159585	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:33

S14	0	JP adj "5159585"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:33
S15	0	JP05159585$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:34
S16	176	"159585"$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:34
S17	59	"159585"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:34
S19	0	JP adj "159585"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:35
S20	0	JP adj2 "159585"$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:35
S21	82	JP$5"159585"$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:36
S22	3	JP adj "05159585"$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:39

S23	85	"5946551"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:43
S24	2	"5946551".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:43
S25	61	("5144473" | "5347144").PN. OR ("5946551").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/01/08 17:44
S26	1	"6387737".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2010/01/08 17:49
S27	2	"6387737".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/08 17:50
S28	329	ferro$electric with (gate adj (dielectric or inulat$5))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 18:52
S31	51	ferro$electric with (gate adj (dielectric or inulat$5)) with capacitor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 18:54
S32	92	(gate adj (dielectric or inulat$5)) with capacitor with ("same" near4 (layer or film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 19:05
S33	2562	gate with capacitor with ("same" near4 (layer or film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 19:09

S34	1448	S33 and organic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 19:09
S35	125	S33 and (organic adj semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 19:10
S36	483	S34 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:08
S37	433	S36 not S35	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:08
S38	385	S37 and (substrate with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:09
S39	107	S37 and (substrate with gate with capacitor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:09
S40	2162	(gate adj (dielectric or inulat$5)) with capacitor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:30
S41	7827	organic with memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:30

S42	51	S40 and S41	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:30
S43	4360	257/40.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:32
S44	2811	257/295.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:34
S45	33	S43 and S44	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:34
S46	2297	257/e27.104,e51.007. ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:53
S47	8566	S43 or S44 or S46	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:53
S48	1319	S47 and (gate with capacitor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:53
S49	901	S48 and ferroelectric	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:53

S50	618	S48 and (ferroelectric with gate with capacitor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 22:54
S51	701	S48 not S50	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 23:06
S52	7247	S47 not S48	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 23:27
S55	2334	S52 and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/01/11 23:27

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